

IN THE DISCLOSURE:

Page 4, please replace the third full paragraph with the following rewritten paragraph:

There are problems when the CoSi_2 is worn away in this manner in that CoSi_2 sheet resistance increases and the fluctuations in resistance become larger, etc. The reason for this is that when titanium nitride film is removed with an ammonia-hydrogen peroxide-water mixture, the film is etched up to the CoSi layer, which is on the bottom of the titanium nitride film, and as a result, the CoSi film becomes thinner, and the CoSi_2 film that is then formed by the second RTA treatment becomes even thinner.

Page 17, please replace the first full paragraph with the following rewritten paragraph:

Next, as shown in Figure 1(C), first RTA treatment is performed, at a temperature within a temperature range of 450°C to 600°C , between each of the cobalt film 20 adjoining diffusion layer 12 and diffusion layer 12 and cobalt film 20 adjoining gate electrode 18 and gate electrode 18 to form CoSi layers 24a, 24b and 26 as a result of the reaction. Part of cobalt film 20 adjoining field insulation film 14 and side walls 19 remains as unreacted cobalt film after this RTA treatment.

Page 18, please replace the second full paragraph with the following rewritten paragraph:

Consequently, it is possible to avoid a subsequent increase in sheet resistance and an increase in fluctuations in resistance of the CoSi_2 that have been formed by the second RTA treatment.

Pages 19 and 20, please replace the fifth full paragraph which continues on page 20 with the following rewritten paragraph:

Next, as shown in Figure 2(C), first RTA treatment is performed, at a temperature within a temperature range of 450°C to 600°C , between each of cobalt film 60 adjoining diffusion layer 52 and diffusion layer 52 and cobalt layer 60 adjoining gate electrode 58 and gate electrode 58 to form CoSi layers 64a, 64b, and 66 as a result of this reaction. Part of cobalt film 60 adjoining field insulation film 54 and side walls 59 remains as unreacted cobalt film after this RTA treatment.

IN THE CLAIMS:

Please amend the claims as follows:

9. (Amended) A method of producing semiconductor devices by cobalt salicide technology with titanium nitride film as the cap film, comprising: